

4V Drive Nch+Nch MOSFET

SH8K22

Structure

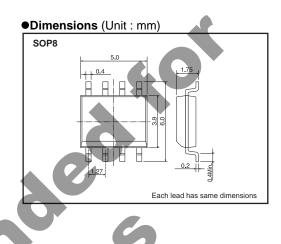
Silicon N-channel MOSFET

Features

1) Built-in G-S Protection Diode. 2) Small surface Mount Package (SOP8).

Application

Power switching, DC / DC converter, Inverter



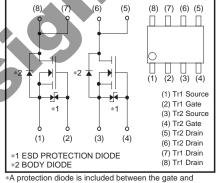
Packaging specifications

	Package	Taping		
Туре	Code	ТВ		
	Basic ordering unit (pieces)	2500		
SH8K22		0		

●Absolute maximum ratings (Ta=25°C)

●Packag	ing specification	ons					
	Package	Taping					
Туре	Code	ТВ					
	Basic ordering unit (p	ieces) 2500	2500				
SH8K22		0					
	te maximum ra	•	Tr2.>		0		
	Parameter		Symbol	Limits	Unit		
Drain-so	urce voltage		V _{DSS}	45	V		
Gate-sou	urce voltage		V _{GSS}	±20	V		
Drain current		Continuous Pulsed	I _D I _{DP} ∗1	±4.5 ±18	A A		
Source c	Source current (Body diode)		Is		A		
(Body die			I _{SP}	18	Α		
Total power dissipation				2	W / TOTAL		
			P _D ∗2	1.4	W / ELEMENT		
Chanel t	emperature		T _{ch}	150	°C		
Range of	f Storage tempe	erature	T _{stg}	-55 to +150	°C		

Inner circuit



the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

*1 PW \leq 10 μ s, Duty cycle \leq 1%

*2 Mounted on a ceramic board

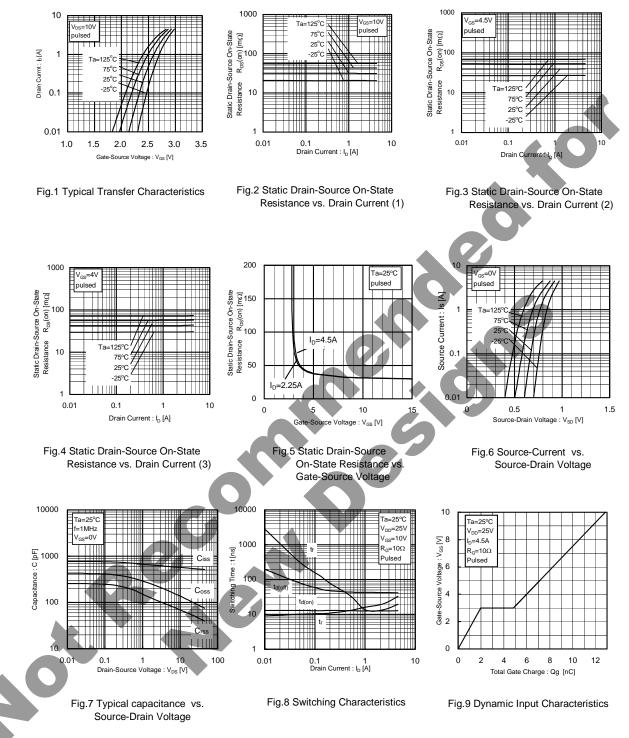
•Electrical characteristics (Ta=25°C) <It is the same characteristics for the Tr1 and Tr2 >

<it characterist<="" is="" same="" th="" the=""><th>ics for tr</th><th>ne i r'i</th><th>and Ir</th><th>2.></th><th></th><th></th><th>_</th></it>	ics for tr	ne i r'i	and Ir	2.>			_
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	Igss	-	-	±10	μA	V _{GS} =±20V, V _{DS} =0V	-
Drain-source breakdown voltage	V(BR) DSS	45	-	-	V	I _D = 1mA, V _{GS} =0V	-
Zero gate voltage drain current	IDSS	_	-	1	μA	VDS= 45V, VGS=0V	-
Gate threshold voltage	VGS (th)	1.0	-	2.5	V	V _{DS} = 10V, I _D = 1mA	-
		-	33	46	mΩ	I _D = 4.5A, V _{GS} = 10V	
Static drain-source on-state resistance	RDS (on)*	-	41	57	mΩ	I _D = 4.5A, V _{GS} = 4.5V	
resistance		_	46	64	mΩ	ID= 4.5A, VGS= 4.0V	
Forward transfer admittance	Y _{fs} *	3.5	-	-	S	V _{DS} = 10V, I _D = 4.5A	
Input capacitance	Ciss	-	550	-	pF	V _{DS} = 10V	
Output capacitance	Coss	-	140	-	pF	V _{GS} =0V	
Reverse transfer capacitance	Crss	_	70	-	pF	f=1MHz	
Turn-on delay time	t _{d (on)} *	-	12	-	ns	Vdd≒25V	
Rise time	tr *	-	18	-	ns	ID= 2.5A Vgs= 10V	
Turn-off delay time	td (off) *	-	42	-	ns	$R_{L}=10\Omega$	
Fall time	tf *	_	12	-	ns	R _g =10Ω	
Total gate charge	Qg *	-	6.8	9.6	nC	V _{DD} ≒25V, V _{GS} =5V	
Gate-source charge	Q _{gs} *	_	2.0	_	nC	I _D = 4.5A	
Gate-drain charge	Q _{gd} *	_	2.9	_	nC	R _L = 5.6Ω, R _G = 10Ω	
Pulsed							

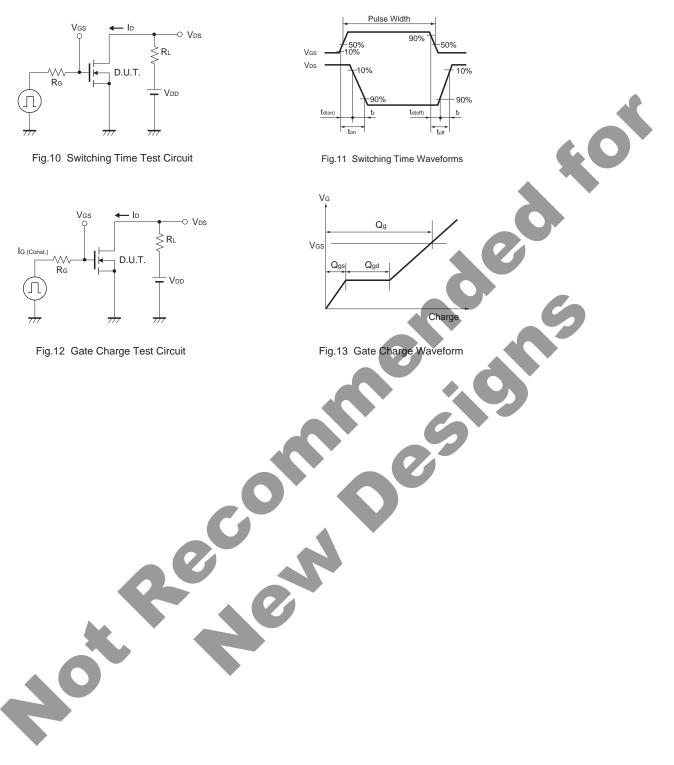
•Body diode characteristics (Source-Drain) (Ta=25°C)

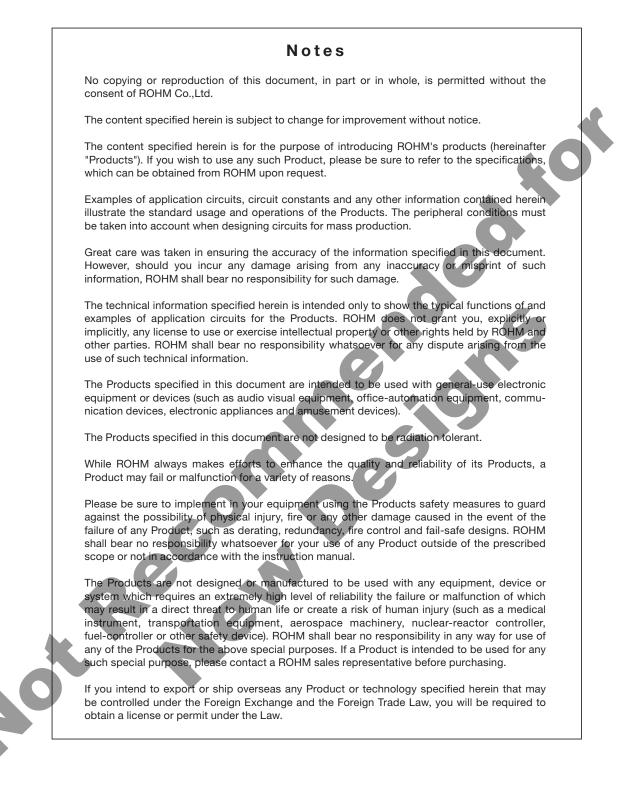
•Body diode characteristic			25°C)			
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Forward voltage	V _{SD} *	_		1.2	V I _S	=4.5A/V _{GS} =0V
* pulsed				5	5	

•Electrical characteristic curves



•Measurement circuits







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